

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N2484 TO-18 CASE
PN2484 TO-92 CASE

NPN SILICON TRANSISTOR

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N/PN 2484 types are Silicon NPN Transistors designed for low noise amplifier applications.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	50	mA
Power Dissipation (TO-18)	P _D	360	mW
Power Dissipation (TO-92)	P _D	625	mW
Operating & Storage Junction Temperature (TO-18)	T _J , T _{stg}	-65 TO +200	°C
Operating & Storage Junction Temperature (TO-92)	T _J , T _{stg}	-65 TO +150	°C
Thermal Resistance	θ _{JA}	0.49	°C/mW
Thermal Resistance	θ _{JA}	0.2	°C/mW

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{CB0}	V _{CB} =45V		10	nA
I _{CB0}	V _{CB} =45V, T _A =150°C		10	μA
I _{CEO}	V _{CE} =5.0V		2.0	nA
I _{EBO}	V _{EB} =5.0V		10	nA
BV _{CB0}	I _C =10μA	60		V
BV _{CEO}	I _C =10mA	60		V
BV _{EBO}	I _E =10μA	6.0		V
V _{CE} (SAT)	I _C =1.0mA, I _B =0.1mA		0.35	V
V _{BE} (ON)	V _{CE} =5.0V, I _C =100μA	0.5	0.7	V
h _{FE}	V _{CE} =5.0V, I _C =1.0μA	30		
h _{FE}	V _{CE} =5.0V, I _C =10μA	100	500	
h _{FE}	V _{CE} =5.0V, I _C =10μA, T _A =-55°C	20		
h _{FE}	V _{CE} =5.0V, I _C =100μA	175		
h _{FE}	V _{CE} =5.0V, I _C =500μA	200		
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	250		
h _{FE}	V _{CE} =5.0V, I _C =10mA		800	
h _{fe}	V _{CE} =5.0V, I _C =1.0mA, f=1.0kHz	150	900	
f _T	V _{CE} =5.0V, I _C =50μA, f=5.0MHz	15		MHz
f _T	V _{CE} =5.0V, I _C =0.5mA, f=30MHz	60		MHz
h _{ie}	V _{CE} =5.0V, I _C =1.0mA, f=1.0kHz	3.5	24	kΩ
h _{oe}	V _{CE} =5.0V, I _C =1.0mA, f=1.0kHz		40	μmhos
h _{re}	V _{CE} =5.0V, I _C =1.0mA, f=1.0kHz		800	x10 ⁻⁶
C _{ob}	V _{CB} =5.0V, I _E =0, f=140kHz		6.0	pF
C _{ib}	V _{EB} =0.5V, I _C =0, f=140kHz		6.0	pF
NF	V _{CE} =5.0V, I _C =10μA, R _S =10KΩ, BW=15.7kHz, 3.0db PTS @ 10Hz, 10kHz		3.0	dB
NF	V _{CE} =5.0V, I _C =10μA, R _S =10KΩ, f=100Hz, BW=20 Hz		10	dB
NF	V _{CE} =5.0V, I _C =10μA, R _S =10KΩ, f=1.0kHz, BW=200Hz		3.0	dB
NF	V _{CE} =5.0V, I _C =10μA, R _S =10KΩ, f=10kHz, BW=2.0kHz		2.0	dB